

In the Claims:

Claim 1 (currently amended): A flash memory device, comprising:

a. a substrate;

b. at least one ~~plurality of~~ core stacks, wherein the at least one ~~each~~ core stack comprises:

- (1) a tunnel oxide layer on the substrate;
- (2) a first polysilicon layer on the tunnel oxide layer;
- (3) an anti-reflective interpoly layer on the first polysilicon layer; and
- (4) a transmissive second polysilicon layer on the anti-reflective

interpoly layer;

c. at least one ~~plurality of~~ source regions adjacent to the at least one ~~plurality~~ of core stacks; and

d. at least one ~~plurality of~~ drain regions adjacent to the at least one ~~plurality of~~ core stacks.

Claim 2 (currently amended): The flash memory device, as recited in Claim 1, wherein the at least one ~~plurality of~~ source regions and the at least one ~~plurality of~~ drain regions are formed by the method comprising the steps of:

a. depositing a layer of photoresist over the substrate and the at least one ~~plurality of~~ core stacks;

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- b. illuminating the layer of photoresist with a light;
- c. transmitting some of the light through the transmissive second polysilicon layer;
- d. preventing the reflection of the light at the anti-reflective interpoly layer;
- e. removing part of the photoresist layer; and
- f. implanting a dopant into the substrate.

Claim 3 (original): The flash memory device, as recited in Claim 2, wherein the light has a wavelength λ_1 , and wherein the anti-reflective interpoly layer has an index of refraction n and a thickness d , and wherein the light has an integer number m wavelengths incident upon the anti-reflective interpoly layer, and wherein

$$d \cong \frac{(m + \frac{1}{2})\lambda_1}{2n}, \text{ where } m = 0, 1, 2, \dots$$

Claim 4 (original): The flash memory device, as recited in Claim 2, wherein the light has a wavelength λ_1 , and wherein the anti-reflective interpoly layer has an index of refraction n , and a thickness d , wherein

$$d \cong \frac{\lambda_1}{4n}.$$

Claim 5 (original): The flash memory device, as recited in Claim 4, wherein the anti-reflective interpoly layer is made of silicon oxynitride (SiON).

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Claim 6 (original): The flash memory device, as recited in Claim 5, wherein the thickness of the anti-reflective interpoly layer is between about 300 to 400 Å thick.

Claim 7 (original): The flash memory device, as recited in Claim 2, wherein the step of depositing the layer of photoresist, deposits the photoresist onto a surface of the transmissive second polysilicon layer.

Claim 8 (original): The flash memory device, as recited in Claim 1, wherein the anti-reflective interpoly layer is made of silicon oxynitride.

Claim 9 (original): The flash memory device, as recited in Claim 8, wherein the thickness of the anti-reflective interpoly layer is between about 300 to 400 Å thick.

Claims 10-15 (canceled)